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(FILE 'USPAT' ENTERED AT 16:46:38 ON 01 AUG 1999)

L1 7 S (HDPCVD OR HDP(W)CVD OR (HIGH(W)DENSITY(W)PLASMA(W)CHEMI
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L2 25 S (HDPCVD OR HDP(W)CVD OR (HIGH(W)DENSITY(W)PLASMA(W)CHEMI
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1. 5,920,792, Jul. 6, 1999, High density plasma enhanced chemical vapor deposition process in combination with chemical mechanical polishing process for preparation and planarization of intermetal dielectric layers; Chi-Fa Lin, 438/633, 692 [IMAGE AVAILABLE]
2. 5,920,791, Jul. 6, 1999, Method of manufacturing intermetal dielectrics for sub-half-micron semiconductor devices; Fu-Liang Yang, et al., 438/622, 624, 631, 706 [IMAGE AVAILABLE]
3. 5,913,140, Jun. 15, 1999, Method for reduction of plasma charging damage during chemical vapor deposition; Gregory A. Roche, et al., 438/624, 761, 788 [IMAGE AVAILABLE]
4. 5,911,834, Jun. 15, 1999, Gas delivery system; Kevin Fairbairn, et al., 134/1.3; 118/715, 719; 134/1.2; 156/345; 427/248.1 [IMAGE AVAILABLE]
5. 5,909,994, Jun. 8, 1999, Vertical dual loadlock chamber; Rick Blum, et al., 414/217; 118/719; 414/416, 937, 939 [IMAGE AVAILABLE]
6. 5,905,302, May 18, 1999, Loadlock cassette with wafer support rails; Christopher Lane, et al., 257/678; 414/217 [IMAGE AVAILABLE]
7. 5,902,088, May 11, 1999, Single loadlock chamber with wafer cooling function; Kevin Fairbairn, et al., 414/217; 118/719; 414/416, 937, 939 [IMAGE AVAILABLE]
8. 5,891,799, Apr. 6, 1999, Method for making stacked and borderless via structures for multilevel metal interconnections on semiconductor substrates; Bing-Yue Tsui, 438/624, 633, 634, 637 [IMAGE AVAILABLE]
9. 5,885,894, Mar. 23, 1999, Method of planarizing an inter-layer dielectric layer; Jiunh-Yuan Wu, et al., 438/624; 427/255.7, 574, 579; 438/633, 692, 699, 761, 763, 778, 784, 787 [IMAGE AVAILABLE]
10. 5,858,869, Jan. 12, 1999, Method for fabricating intermetal dielectric insulation using anisotropic plasma oxides and low dielectric constant polymers; Lai-Juh Chen, et al., 438/597, 618, 622 [IMAGE AVAILABLE]
11. 5,855,681, Jan. 5, 1999, Ultra high throughput wafer vacuum processing system; Dan Maydan, et al., 118/719; 156/345; 204/298.25, 298.35 [IMAGE AVAILABLE]
12. 5,851,899, Dec. 22, 1998, Gapfill and planarization process for shallow trench isolation; Peter Weigand, 438/427, 424, 692, 788 [IMAGE AVAILABLE]
13. 5,844,195, Dec. 1, 1998, Remote plasma source; Kevin Fairbairn, et al., 219/121.43; 156/345; 204/298.38; 219/121.4, 121.51 [IMAGE AVAILABLE]

~~14.~~ 5,843,836, Dec. 1, 1998, Tunneling technology for reducing intra-conductive layer capacitance; Robin W. Cheung, et al., 438/626, 668, 700 [IMAGE AVAILABLE]

15. 5,838,121, Nov. 17, 1998, Dual blade robot; Kevin Fairbairn, et al., 318/45; 74/490.03; 318/568.11, 625; 464/29; 901/14, 23 [IMAGE AVAILABLE]

16. 5,811,356, Sep. 22, 1998, Reduction in mobile ion and metal contamination by varying season time and bias RF power during chamber cleaning; Laxman Murugesu, et al., 438/711; 134/1.1, 4; 216/67; 438/905 [IMAGE AVAILABLE]

17. 5,804,259, Sep. 8, 1998, Method and apparatus for depositing a multilayered low dielectric constant film; Stuardo Robles, 427/577, 122, 249.7, 255.6, 255.7, 906; 438/584, 763, 780, 784 [IMAGE AVAILABLE]

18. 5,800,621, Sep. 1, 1998, Plasma source for HDP-CVD chamber; Fred C. Redeker, et al., 118/723AN, 723I; 156/345; 315/111.51 [IMAGE AVAILABLE]

19. 5,772,771, Jun. 30, 1998, Deposition chamber for improved deposition thickness uniformity; Shijian Li, et al., 118/723I, 715; 204/298.07 [IMAGE AVAILABLE]

20. 5,759,906, Jun. 2, 1998, Planarization method for intermetal dielectrics between multilevel interconnections on integrated circuits; Chine-Gie Lou, 438/623, 624, 626, 627, 633, 639 [IMAGE AVAILABLE]

21. 5,730,803, Mar. 24, 1998, Apparatus and method for transferring heat from a hot electrostatic chuck to an underlying cold body; Robert Steger, et al., 118/723R; 29/25.01; 118/723E, 724, 725, 728; 156/345 [IMAGE AVAILABLE]

22. 5,721,173, Feb. 24, 1998, Method of forming a shallow trench isolation structure; Hiroyuki Yano, et al., 438/424, 221, 296, 759, 788 [IMAGE AVAILABLE]

~~23.~~ 5,679,606, Oct. 21, 1997, method of forming inter-metal-dielectric structure; Chin-Kun Wang, et al., 438/763, 624, 788 [IMAGE AVAILABLE]

24. 5,670,828, Sep. 23, 1997, Tunneling technology for reducing intra-conductive layer capacitance; Robin W. Cheung, et al., 257/773, 776 [IMAGE AVAILABLE]

25. 5,661,093, Aug. 26, 1997, Method for the stabilization of halogen-doped films through the use of multiple sealing layers; Kramadhati V. Ravi, et al., 438/763; 427/255.7, 579; 438/784, 788 [IMAGE AVAILABLE]